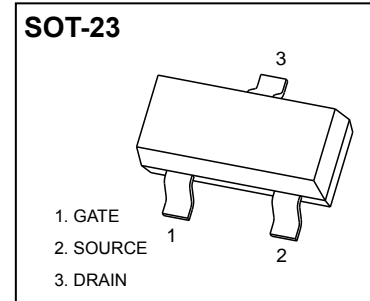


SOT-23 Plastic-Encapsulate MOSFETS

N Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100V	6Ω@10V	0.17A
	10Ω@4.5V	



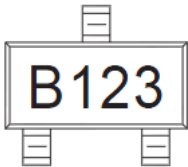
FEATURE

- Surface Mount Package
- High Density Cell Design for Extremely Low $R_{DS(ON)}$
- Voltage Controlled Small Signal Switch
- Rugged and Reliable

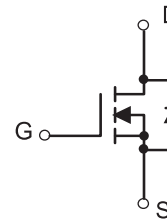
APPLICATION

- Small Servo Motor Controls
- Power MOSFET Gate Drivers
- Switching Application

MARKING



Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
N-MOSFET			
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current (note 1)	I_D	0.17	A
Pulsed Drain Current ($t_p=10\mu s$)	I_{DM}	0.68	A
Continuous Source-Drain Diode Current	I_S	0.17	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	357	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}C$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^{\circ}C$



MOSFET ELECTRICAL CHARACTERISTICS

T_a = 25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V			10	nA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±50	nA
Gate threshold voltage (note 2)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.6	2.8	V
Drain-source on-resistance(note 2)	R _{DS(on)}	V _{GS} = 4.5V, I _D = 0.17A		3.8	10	Ω
		V _{GS} = 10V, I _D = 0.17A		3.5	6	Ω
Forward tranconductance(note 2)	g _{FS}	V _{DS} = 10V, I _D = 170mA	80			mS
Diode forward voltage	V _{SD}	I _S = 340mA, V _{GS} = 0V			1.3	V
DYNAMIC CHARACTERISTICS (note 4)						
Input Capacitance	C _{iSS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		29	60	pF
Output Capacitance	C _{oSS}			10	15	pF
Reverse Transfer Capacitance	C _{rSS}			2	6	pF
SWITCHING CHARACTERISTICS (note 3,4)						
Turn-on delay time	t _{d(on)}	V _{GS} = 10V, V _{DD} = 30V, I _D = 0.28A, R _{GEN} = 50 Ω			8	ns
Turn-on rise time	t _r				8	ns
Turn-off delay time	t _{d(off)}				13	ns
Turn-off fall time	t _f				16	ns
Total Gate Charge	Q _g	V _{DS} = 10V, I _D = 0.22A, V _{GS} = 10V		1.4	2	nC
Gate-Source Charge	Q _{gs}			0.15	0.25	nC
Gate-Drain Charge	Q _{gd}			0.2	0.4	nC

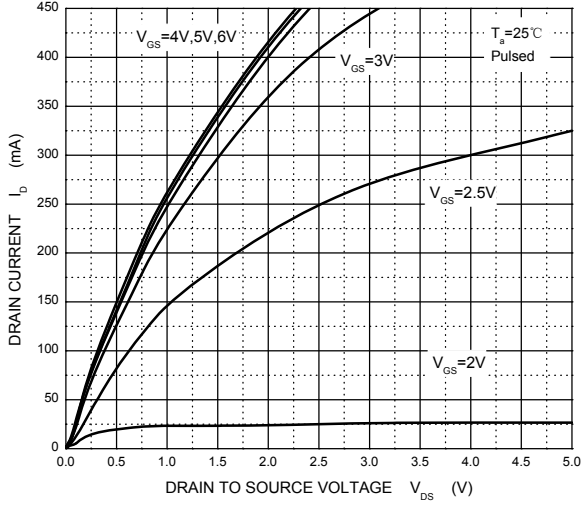
Notes :

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse width = 300μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperature.
4. Granted by design, not subject to producing.

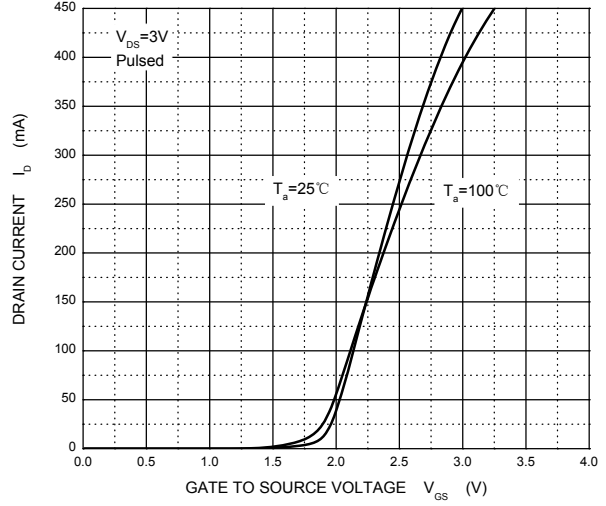


Typical Characteristics

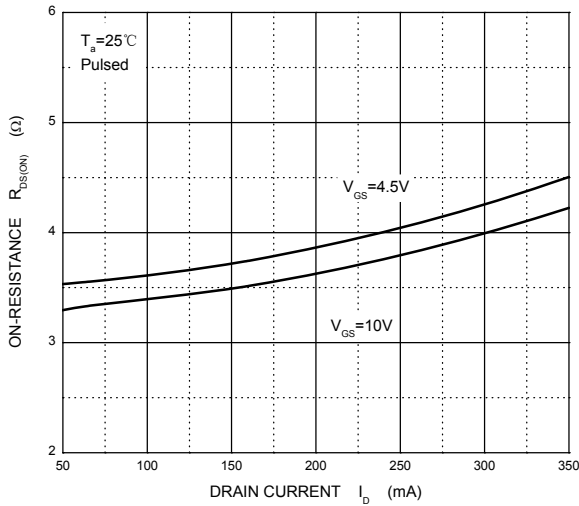
Output Characteristics



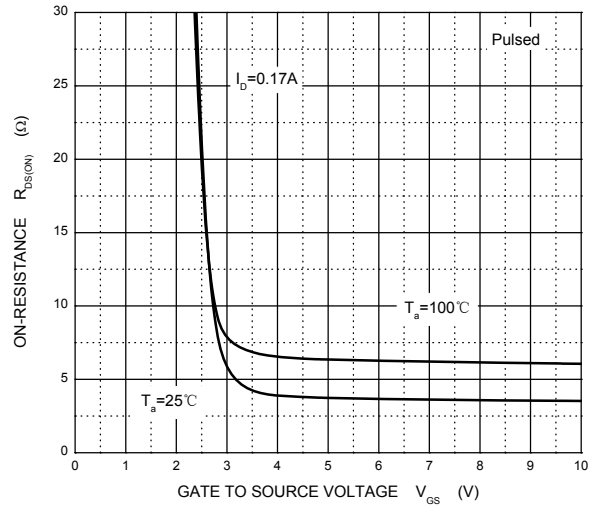
Transfer Characteristics



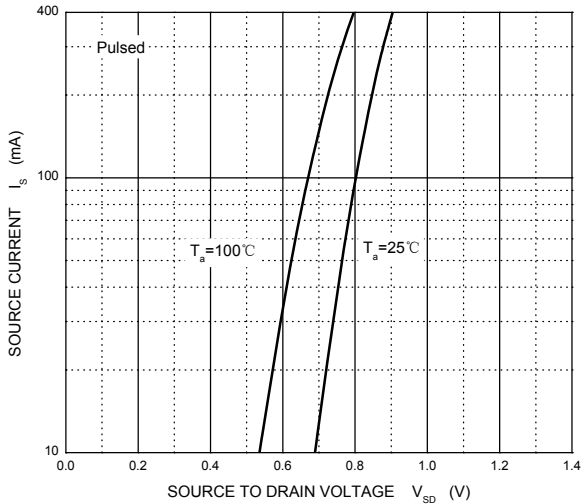
R_DS(ON) — I_D



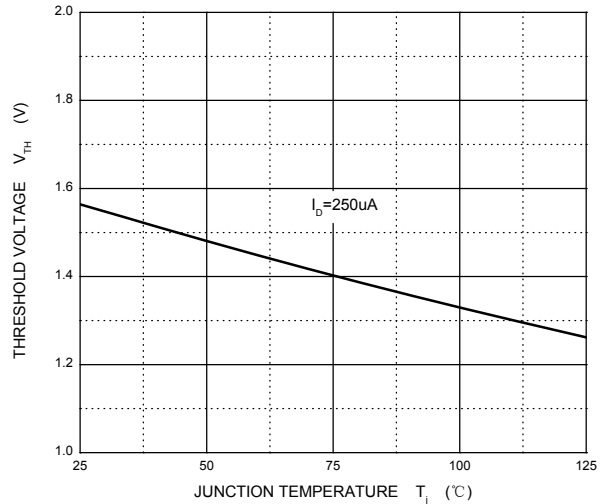
R_DS(ON) — V_GS



I_S — V_SD



Threshold Voltage

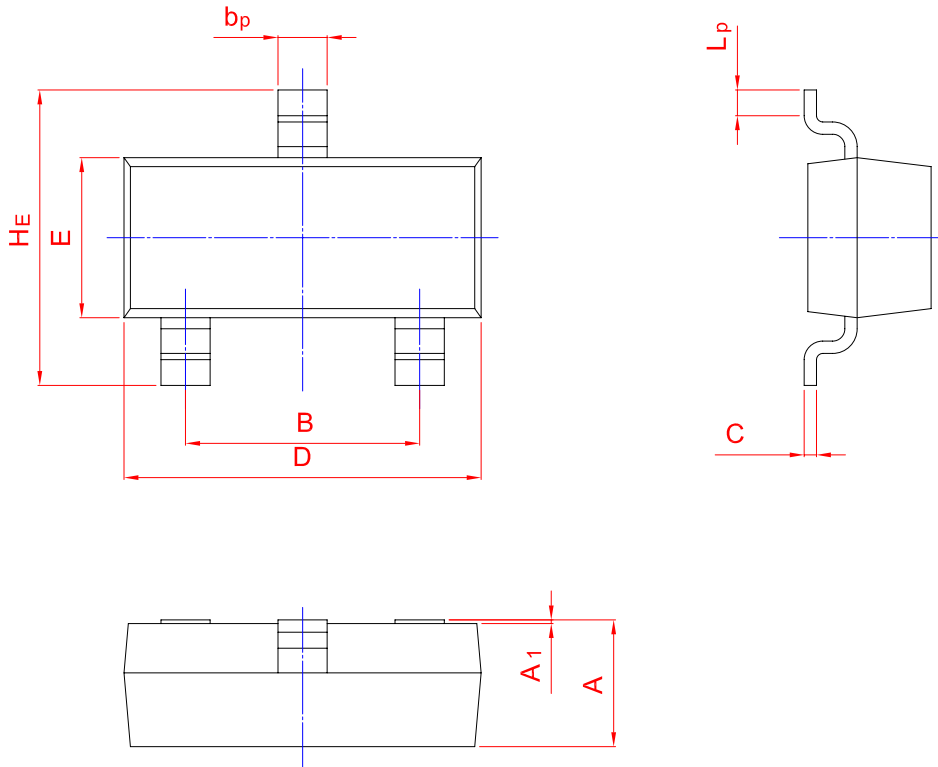
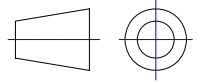




PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20